

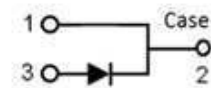
### ◆ Features

- Negligible reverse recovery
- High-speed switching
- Positive Temperature Coefficient
- Temperature-Independent Switching
- Pb-free / RoHS compliant

650V SILICON CARBIDE  
SCHOTTKY DIODE  
V<sub>RRM</sub> 650V  
I<sub>F</sub> 8A (T<sub>C</sub>=141°C)  
Q<sub>C</sub> 23nC

### ◆ Benefits

- Higher frequency
- Low heat dissipation requirements
- Reduce size and cost of the system
- High-reliability



ITO-220AC

### Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	Note	
V <sub>RRM</sub>	Repetitive peak reverse voltage	650	V		
I <sub>F</sub>	Continuous forward current	T <sub>c</sub> =25°C	20	A	Figure 3
		T <sub>c</sub> =135°C	9	A	
		T <sub>c</sub> =141°C	8	A	
I <sub>FSM</sub>	Non-repetitive forward surge current	T <sub>c</sub> =25°C, t <sub>p</sub> =10ms, Half sine pulse	75	A	
		T <sub>c</sub> =110°C, t <sub>p</sub> =10ms, Half sine pulse	67	A	
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	T <sub>c</sub> =25°C, t <sub>p</sub> =10ms, Half sine pulse	73	A	
∫ i <sup>2</sup> dt	i <sup>2</sup> t value	T <sub>c</sub> =25°C, t <sub>p</sub> =10ms	28	A <sup>2</sup> S	
		T <sub>c</sub> =110°C, t <sub>p</sub> =10ms	22	A <sup>2</sup> S	
P <sub>tot</sub>	Power Dissipation	T <sub>c</sub> =25°C	70	W	Figure 4
		T <sub>c</sub> =110°C	30	W	
		T <sub>c</sub> =150°C	10	W	
T <sub>j</sub> , T <sub>stg</sub>	Operating and Storage Temperature	-55 to +175	°C		

**Electrical Characteristics (Tc=25°C unless otherwise noted)**

Symbol	Parameter	Test Conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{DC}$	DC blocking voltage		650	-	-	V	
$V_F$	Forward voltage	$I_F=4A$	-	1.18	-	V	Figure 1
		$I_F=8A, T_c=25^\circ C$	-	1.39	1.6	V	
		$I_F=8A, T_c=175^\circ C$		1.74		V	
$I_R$	Reverse current	$V_R=650V, T_c=25^\circ C$	-	6	60	$\mu A$	Figure 2
		$V_R=650V, T_c=175^\circ C$		12		$\mu A$	
$Q_C$	Total capacitive charge	$V_R=400V$	-	23	-	nC	Figure 6
C	Total capacitance	$V_R=1V, f=1MHZ$	-	338	-	pF	Figure 5
		$V_R=200V, f=1MHZ$	-	44	-	pF	
		$V_R=400V, f=1MHZ$	-	43	-	pF	
$E_C$	Capacitance Stored Energy	$V_R=400V$	-	3.7	-	$\mu J$	Figure 7

**Thermal Characteristics**

Symbol	Parameter	Value		Unit	Note
		Typ.	Max.		
$R_{th(j-c)}$	Thermal resistance (Junction to case)	2.1	-	$^\circ C/W$	Figure 8

**Electrical Characteristic Curves**

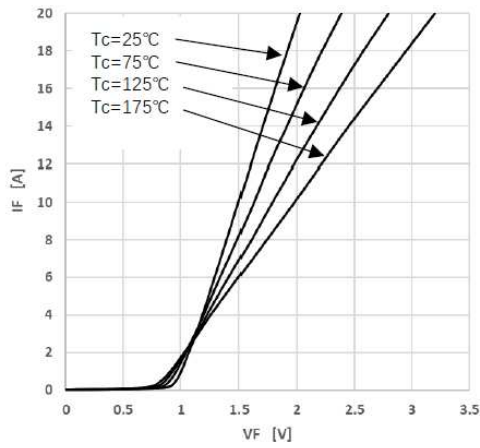


Figure 1 Forward Characteristics

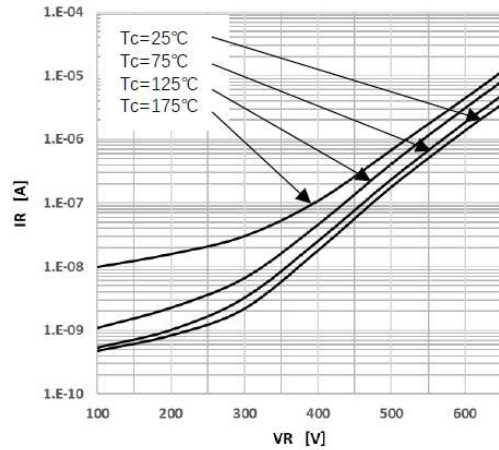


Figure 2 Reverse Characteristics

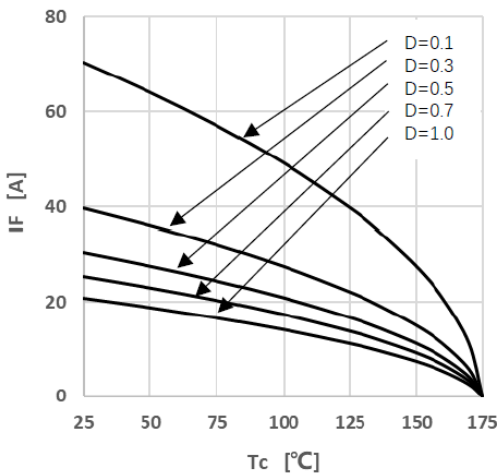


Figure 3 Peak Forward Current Derating

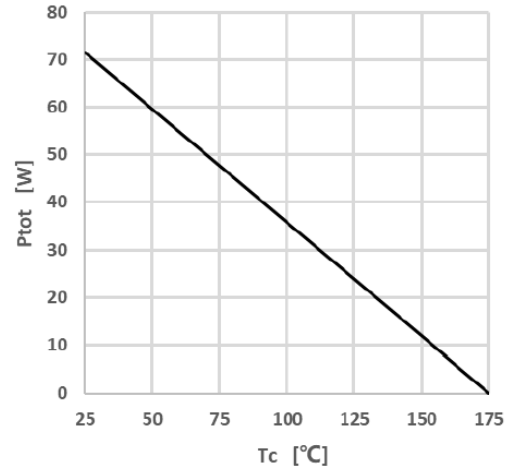


Figure 4 Power Dissipation

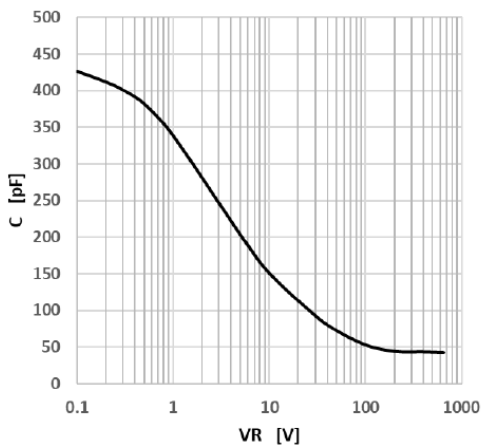


Figure 5 Capacitance vs. Reverse Voltage

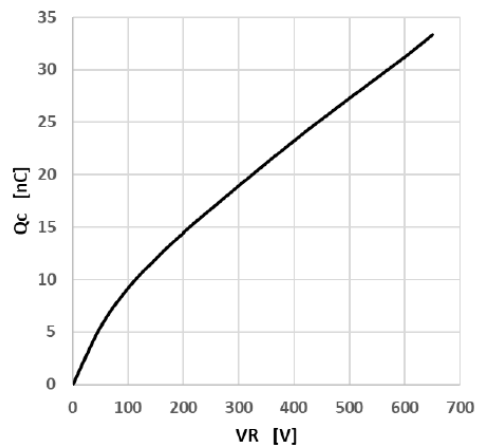


Figure 6 Capacitance Charge vs. Reverse Voltage

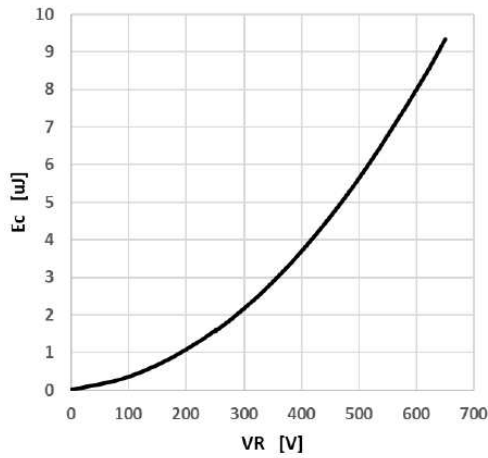


Figure 7 Capacitance Stored Energy

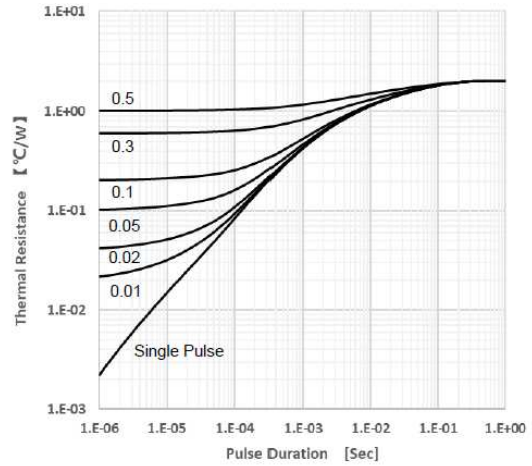
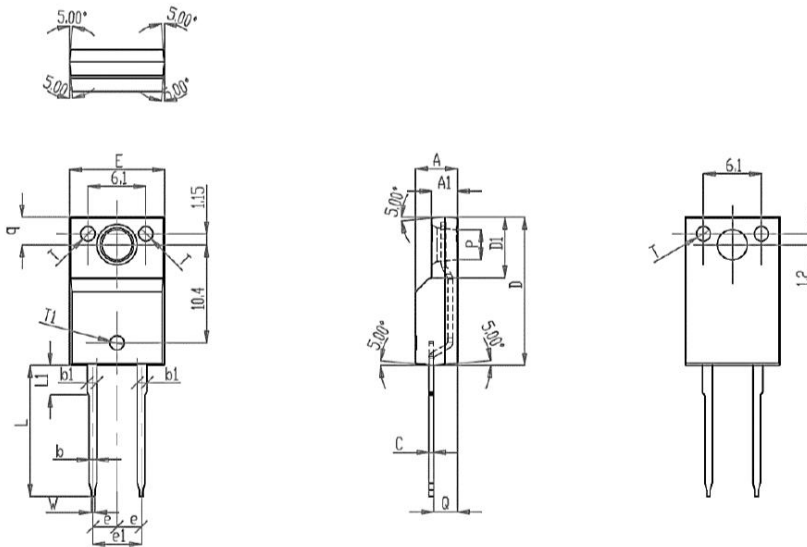


Figure 8 Transient Thermal Impedance

ITO-220AC Package Dimensions : (Unit : mm)



SYMBOL	MILLIMETERS			NOTES	SYMBOL	MILLIMETERS			NOTES
	Normal	MIN.	MAX.			Normal	MIN.	MAX.	
A	4.4	4.2	4.6		e1	5.08	5	5.12	
A1	2.7	2.5	2.9		L	13.90	13.5	14.4	
b	0.8	0.7	0.9		L1	3.12	2.8	3.3	
b1	1.07	0.9	1.3		P	3.14	3.00	3.20	
C	0.5	0.4	0.6		Q	2.44	2.3	2.6	
D	15.63	15.4	15.8		q	2.87	2.6	3	
D1	6.22	6	6.4		W	0.37	0.3	0.5	
E	10.06	9.7	10.3		T	1.52	1.3	1.7	
e	2.54	2.5	2.58		T1	1.20	1.1	1.3	